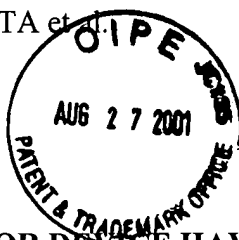


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: A. KURAMATA et al.

Serial Number: 09/313,764

Filed: May 18, 1999



Group Art Unit: 2823

Examiner: W. Coleman

#13/Amend  
Atrial  
9/6/01  
RECEIVED  
AUG 30 2001  
TECHNOLOGY CENTER 2800

For: **OPTICAL SEMICONDUCTOR DEVICE HAVING AN EPITAXIAL LAYER OF III-V COMPOUND SEMICONDUCTOR MATERIAL CONTAINING N AS A GROUP V ELEMENT**

AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Date: August 27, 2001

Sir:

In response to the Office Action dated April 25, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) An optical semiconductor device, comprising:
- a substrate of SiC having a first conductivity type;
  - a buffer layer of AlGa<sub>x</sub>N formed on said substrate epitaxially, said buffer layer having said first conductivity type and a composition represented by a compositional parameter x as Al<sub>x</sub>Ga<sub>1-x</sub>N;